## DESCRIPTION

Monolithic temperature and overload protected logic level power MOSFET in TOPFET2 technology assembled in a 3 pin surface mount plastic package.

## APPLICATIONS

General purpose switch for driving

- lamps
- motors
- solenoids
- heaters
in automotive systems and other applications.


## FEATURES

- TrenchMOS output stage
- Current limiting
- Overload protection
- Overtemperature protection
- Protection latched reset by input
- 5 V logic compatible input level
- Control of output stage and supply of overload protection circuits derived from input
- Low operating input current permits direct drive by micro-controller
- ESD protection on all pins
- Overvoltage clamping for turn off of inductive loads


## QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | UNIT |
| :--- | :--- | :---: | :---: |
|  | Continuous drain source voltage | 50 | V |
| $\mathrm{~V}_{\mathrm{DS}}$ | Continuous drain current | 8 | A |
| $\mathrm{I}_{\mathrm{D}}$ | Total power dissipation | 40 | W |
| $\mathrm{P}_{\mathrm{D}}$ | Continuous junction temperature | 150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{j}}$ | Drain-source on-state resistance | 100 | $\mathrm{~m} \Omega$ |
| $\mathrm{R}_{\mathrm{DS}(\mathrm{ON})}$ | Input supply current | $\mathrm{V}_{\mathrm{IS}}=5 \mathrm{~V}$ | 650 |
| $\mathrm{I}_{\text {ISL }}$ |  | $\mu \mathrm{A}$ |  |
|  |  |  |  |
|  |  |  |  |
|  |  |  |  |
|  |  |  |  |

FUNCTIONAL BLOCK DIAGRAM


Fig.1. Elements of the TOPFET.

## PIN CONFIGURATION



SYMBOL


## Logic level TOPFET

## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
| :--- | :--- | :--- | :---: | :---: | :---: |
| $\mathrm{V}_{\text {DS }}$ | Continuous drain source voltage ${ }^{1}$ | - | - | 50 | V |
| $\mathrm{I}_{\mathrm{D}}$ | Continuous drain current | $\mathrm{V}_{\text {IS }}=5 \mathrm{~V} ; \mathrm{T}_{\mathrm{mb}}=25^{\circ} \mathrm{C}$ | - | self | A |
|  |  | $\mathrm{V}_{\text {IS }}=5 \mathrm{~V} ; \mathrm{T}_{\mathrm{mb}} \leq 110^{\circ} \mathrm{C}$ | - | 8 | 8 |
| $\mathrm{I}_{\mathrm{D}}$ | Continuous drain current | A |  |  |  |
| $\mathrm{I}_{\mathrm{I}}$ | Continuous input current | - | -5 | 5 | mA |
| $\mathrm{I}_{\text {IRM }}$ | Non-repetitive peak input current | $\mathrm{t}_{\mathrm{p}} \leq 1 \mathrm{~ms}$ | -10 | 10 | mA |
| $\mathrm{P}_{\mathrm{D}}$ | Total power dissipation | $\mathrm{T}_{\mathrm{mb}} \leq 25^{\circ} \mathrm{C}$ | - | 40 | W |
| $\mathrm{~T}_{\text {stg }}$ | Storage temperature | - | -55 | 175 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{j}}$ | Continuous junction temperature ${ }^{2}$ | normal operation | - | 150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {sold }}$ | Case temperature | during soldering | - | 260 | ${ }^{\circ} \mathrm{C}$ |

## ESD LIMITING VALUE

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
| :--- | :--- | :--- | :---: | :---: | :---: |
| V $_{\mathrm{C}}$ | Electrostatic discharge capacitor <br> voltage | Human body model; <br> $\mathrm{C}=250 \mathrm{pF} ; \mathrm{R}=1.5 \mathrm{k} \Omega$ | - | 2 | kV |

## OVERVOLTAGE CLAMPING LIMITING VALUES

At a drain source voltage above 50 V the power MOSFET is actively turned on to clamp overvoltage transients.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
| :--- | :--- | :--- | :---: | :---: | :---: |
|  | Inductive load turn-off | $\mathrm{D}_{\mathrm{DM}}=8 \mathrm{~A} ; \mathrm{V}_{\mathrm{DD}} \leq 20 \mathrm{~V}$ |  |  |  |
| $\mathrm{E}_{\text {DSM }}$ | Non-repetitive clamping energy | $\mathrm{T}_{\mathrm{mb}} \leq 25^{\circ} \mathrm{C}$ | - | 100 | mJ |
| $\mathrm{E}_{\text {DRM }}$ | Repetitive clamping energy | $\mathrm{T}_{\mathrm{mb}} \leq 95^{\circ} \mathrm{C} ; \mathrm{f}=250 \mathrm{~Hz}$ | - | 20 | mJ |

## OVERLOAD PROTECTION LIMITING VALUE

With an adequate protection supply provided via the input pin, TOPFET can protect itself from two types of overload - overtemperature and short circuit load.

| SYMBOL | PARAMETER | REQUIRED CONDITION | MIN. | MAX. | UNIT |
| :--- | :--- | :--- | :---: | :---: | :---: |
| $\mathrm{V}_{\text {DS }}$ | Drain source voltage $^{3}$ | $4 \mathrm{~V} \leq \mathrm{V}_{\text {IS }} \leq 5.5 \mathrm{~V}$ | 0 | 35 | V |

## THERMAL CHARACTERISTIC

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| :--- | :--- | :--- | :---: | :---: | :---: | :---: |
|  | Thermal resistance | - |  |  |  | K |
| $R_{t \mathrm{th} \mathrm{j} \cdot \mathrm{mb}}$ | Junction to mounting base | - | - | 2.5 | 3.1 | K/W |
| $\mathrm{R}_{\mathrm{th} \mathrm{j}-\mathrm{a}}$ | Junction to ambient | minimum footprint FR4 PCB | - | 71.4 | - | K/W |

[^0]
## Logic level TOPFET

## OUTPUT CHARACTERISTICS

Limits are for $-40^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{mb}} \leq 150^{\circ} \mathrm{C}$; typicals are for $\mathrm{T}_{\mathrm{mb}}=25^{\circ} \mathrm{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS |  | MIN. | TYP. | MAX. | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {(C)IDSs }}$ | Off-state <br> Drain-source clamping voltage | $\mathrm{V}_{\text {IS }}=0 \mathrm{~V}$ |  |  |  |  |  |
|  |  | $\mathrm{I}_{\mathrm{D}}=10 \mathrm{~mA}$ |  | 50 | - | - | V |
|  |  | $\mathrm{l}_{\mathrm{D}}=1 \mathrm{~A} ; \mathrm{t}_{\mathrm{p}} \leq 300 \mu \mathrm{~s} ; \delta \leq 0.01$ |  | 50 | 60 | 70 | V |
| $\mathrm{l}_{\text {Dss }}$ | Drain source leakage current | $\mathrm{V}_{\mathrm{DS}}=40 \mathrm{~V}$ |  | - | - | 100 | $\mu \mathrm{A}$ |
|  |  |  | $\mathrm{T}_{\mathrm{mb}}=25^{\circ} \mathrm{C}$ | - | 0.1 | 10 | $\mu \mathrm{A}$ |
| $\mathrm{R}_{\text {DS(ON) }}$ | On-state <br> Drain-source resistance | $\mathrm{I}_{\text {DM }}=3 \mathrm{~A} ; \mathrm{t}_{\mathrm{p}} \leq 300 \mu \mathrm{~s} ; \delta \leq 0.01$ |  |  |  |  |  |
|  |  | $\mathrm{V}_{\text {IS }} \geq 4.4 \mathrm{~V}$ |  | - | - | 190 | $\mathrm{m} \Omega$ |
|  |  |  | $\mathrm{T}_{\mathrm{mb}}=25^{\circ} \mathrm{C}$ | - | 68 | 100 | $\mathrm{m} \Omega$ |
|  |  | $\mathrm{V}_{\text {IS }} \geq 4 \mathrm{~V}$ |  | - | - | 200 | $\mathrm{m} \Omega$ |
|  |  |  | $\mathrm{T}_{\mathrm{mb}}=25^{\circ} \mathrm{C}$ | - | 72 | 105 | $\mathrm{m} \Omega$ |

## OVERLOAD CHARACTERISTICS

$-40^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{mb}} \leq 150^{\circ} \mathrm{C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{I}_{\mathrm{D}}$ | Short circuit load Drain current limiting | $\begin{array}{ll} \hline \mathrm{V}_{\mathrm{DS}}=13 \mathrm{~V} & \\ \mathrm{~V}_{\text {IS }}=5 \mathrm{~V} \mathrm{~V}^{2} \leq 5.5 \mathrm{~V} & \mathrm{~T}_{\mathrm{mb}}=25^{\circ} \mathrm{C} \\ 4.4 \mathrm{~V} \leq \mathrm{V}_{\text {IS }} \leq 5.5 \mathrm{~V} & \\ 4 \mathrm{~V} \leq \mathrm{V}_{\text {IS }} \leq 5.5 \mathrm{~V} & \end{array}$ | $\begin{aligned} & 8 \\ & 6 \\ & 5 \end{aligned}$ | $12$ | $\begin{aligned} & 16 \\ & 18 \\ & 18 \end{aligned}$ | $\begin{aligned} & \mathrm{A} \\ & \mathrm{~A} \\ & \mathrm{~A} \end{aligned}$ |
| $\begin{aligned} & \mathrm{P}_{\mathrm{D} \text { (TO) }} \\ & \mathrm{T}_{\mathrm{DSC}} \end{aligned}$ | Overload protection Overload power threshold Characteristic time | $\mathrm{V}_{\mathrm{IS}}=5 \mathrm{~V} ; \quad \mathrm{T}_{\mathrm{mb}}=25^{\circ} \mathrm{C}$ <br> device trips if $P_{D}>\mathrm{P}_{\mathrm{D} \text { (T) }}$ which determines trip time ${ }^{1}$ | $\begin{gathered} 20 \\ 200 \end{gathered}$ | $\begin{gathered} 55 \\ 350 \end{gathered}$ | $\begin{gathered} 80 \\ 600 \end{gathered}$ | $\begin{aligned} & \mathrm{W} \\ & \mu \mathrm{~s} \end{aligned}$ |
| $\mathrm{T}_{\text {j(T) }}$ | Overtemperature protection <br> Threshold junction temperature ${ }^{2}$ |  | 150 | 170 | - | ${ }^{\circ} \mathrm{C}$ |

[^1]
## Logic level TOPFET

## INPUT CHARACTERISTICS

The supply for the logic and overload protection is taken from the input.
Limits are for $-40^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{mb}} \leq 150^{\circ} \mathrm{C}$; typicals are for $\mathrm{T}_{\mathrm{mb}}=25^{\circ} \mathrm{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS |  | MIN. | TYP. | MAX. | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {IS(T) }}$ | Input threshold voltage | $\mathrm{V}_{\mathrm{DS}}=5 \mathrm{~V} ; \mathrm{I}_{\mathrm{D}}=1 \mathrm{~mA}$ |  | 0.6 | - | 2.4 | V |
|  |  |  | $\mathrm{T}_{\mathrm{mb}}=25^{\circ} \mathrm{C}$ | 1.1 | 1.6 | 2.1 | V |
| $\mathrm{I}_{1}$ | Input supply current | normal operation; | $\mathrm{V}_{1 \text { S }}=5 \mathrm{~V}$ | 100 | 220 | 400 | $\mu \mathrm{A}$ |
|  |  |  | $\mathrm{V}_{\text {IS }}=4 \mathrm{~V}$ | 80 | 195 | 330 | $\mu \mathrm{A}$ |
| ISL | Input supply current | protection latched; | $\begin{aligned} & \mathrm{V}_{\text {IS }}=5 \mathrm{~V} \\ & \mathrm{~V}_{\text {IS }}=3 \mathrm{~V} \end{aligned}$ | 200 | 400 | 650 | $\mu \mathrm{A}$ |
|  |  |  |  | 130 | 250 | 430 | $\mu \mathrm{A}$ |
| $\mathrm{V}_{\text {ISR }}$ | Protection reset voltage ${ }^{1}$ | reset time $\mathrm{t}_{\mathrm{r}} \geq 100 \mu \mathrm{~s}$ |  | 1.5 | 2 | 2.9 | V |
| $\mathrm{tr}_{\mathrm{r}}$ | Latch reset time | $\mathrm{V}_{\text {IS } 1}=5 \mathrm{~V}, \mathrm{~V}_{152}<1 \mathrm{~V}$ |  | 10 | 40 | 100 | $\mu \mathrm{s}$ |
| $\mathrm{V}_{\text {(CL) }}$ | Input clamping voltage | $\mathrm{I}_{1}=1.5 \mathrm{~mA}$ |  | 5.5 | - | 8.5 | V |
| $\mathrm{R}_{\mathrm{IG}}$ | Input series resistance ${ }^{2}$ to gate of power MOSFET |  | $\mathrm{T}_{\mathrm{mb}}=25^{\circ} \mathrm{C}$ | - | 33 | - | $\mathrm{k} \Omega$ |

## SWITCHING CHARACTERISTICS

$\mathrm{T}_{\mathrm{mb}}=25^{\circ} \mathrm{C} ; \mathrm{V}_{\mathrm{DD}}=13 \mathrm{~V}$; resistive load $\mathrm{R}_{\mathrm{L}}=4 \Omega$. Refer to waveform figure and test circuit.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| :--- | :--- | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\text {don }}$ | Turn-on delay time | $\mathrm{V}_{\text {IS }}=5 \mathrm{~V}$ | - | 10 | 20 | $\mu \mathrm{~s}$ |
| $\mathrm{t}_{\mathrm{r}}$ | Rise time |  | - | 20 | 40 | $\mu \mathrm{~s}$ |
| $\mathrm{t}_{\text {doff }}$ | Turn-off delay time | $\mathrm{V}_{\text {Is }}=0 \mathrm{~V}$ |  | - | 30 | 60 |
| $\mathrm{t}_{\mathrm{f}}$ | Fall time | $\mu \mathrm{s}$ |  |  |  |  |

[^2]
## MECHANICAL DATA

Plastic single-ended surface mounted package (Philips version of D-PAK); 3 leads (one lead cropped)


Fig.2. SOT428 surface mounting package ${ }^{1}$, centre pin connected to mounting base.

[^3]
## DEFINITIONS

| DATA SHEET STATUS |  |  |  |
| :--- | :--- | :--- | :---: |
| DATA SHEET <br> STATUS' | PRODUCT <br> STATUS |  |  |
| Objective data | Development | This data sheet contains data from the objective specification for <br> product development. Philips Semiconductors reserves the right to <br> change the specification in any manner without notice |  |
| Preliminary data | Qualification | This data sheet contains data from the preliminary specification. <br> Supplementary data will be published at a later date. Philips <br> Semiconductors reserves the right to change the specification without <br> notice, in ordere to improve the design and supply the best possible <br> product |  |
| Product data | This data sheet contains data from the product specification. Philips <br> Semiconductors reserves the right to make changes at any time in <br> order to improve the design, manufacturing and supply. Changes will <br> be communicated according to the Customer Product/Process <br> Change Notification (CPCN) procedure SNW-SQ-650A |  |  |
|  |  |  |  |
| Limiting values | Production |  |  |
| Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one <br> or more of the limiting values may cause permanent damage to the device. These are stress ratings only and <br> operation of the device at these or at any other conditions above those given in the Characteristics sections of <br> this specification is not implied. Exposure to limiting values for extended periods may affect device reliability. |  |  |  |
| Application information | Where application information is given, it is advisory and does not form part of the specification. |  |  |
| © Philips Electronics N.V. 2001 |  |  |  |
| All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the <br> copyright owner. |  |  |  |
| The information presented in this document does not form part of any quotation or contract, it is believed to be <br> accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any <br> consequence of its use. Publication thereof does not convey nor imply any license under patent or other <br> industrial or intellectual property rights. |  |  |  |

## LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

[^4]
[^0]:    1 Prior to the onset of overvoltage clamping. For voltages above this value, safe operation is limited by the overvoltage clamping energy.
    2 A higher $\mathrm{T}_{\mathrm{j}}$ is allowed as an overload condition but at the threshold $\mathrm{T}_{\mathrm{j}(\mathrm{TO})}$ the over temperature trip operates to protect the switch.
    3 All control logic and protection functions are disabled during conduction of the source drain diode.

[^1]:    1 Trip time $t_{d s c}$ varies with overload dissipation $P_{D}$ according to the formula $t_{d s c} \approx T_{D S C} / \ln \left[P_{D} / P_{D(T O)}\right]$.
    2 This is independent of the $\mathrm{dV} / \mathrm{dt}$ of input voltage $\mathrm{V}_{\text {IS }}$.

[^2]:    1 The input voltage below which the overload protection circuits will be reset
    2 Not directly measureable from device terminals.

[^3]:    1 Epoxy meets UL94 V0 at 1/8". Net mass: 1.1 g .
    For soldering guidelines and SMD footprint design, please refer to Data Handbook SC18.

[^4]:    1 Please consult the most recently issued datasheet before initiating or completing a design.
    2 The product status of the device(s) described in this datasheet may have changed since this datasheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

